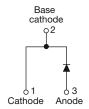
HALOGEN FREE



Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt®

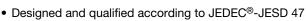




PRIMARY CHARACTERISTICS								
I _{F(AV)}	8 A							
V_{R}	600 V							
V _F at I _F	1.4 V							
t _{rr} (typ.)	15 ns							
T _J max.	175 °C							
Package	2L TO-220AC							
Circuit configuration	Single							

FEATURES

- · Hyperfast recovery time
- Benchmark ultra low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current



 Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recover time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Repetitive peak reverse voltage	V_{RRM}		600	V					
Average rectified forward current	I _{F(AV)}	T _C = 143 °C	8						
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	110	Α					
Repetitive peak forward current	I _{FM}		18						
Operating junction and storage temperatures	T_J , T_{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	.,				
Forward voltage	V _F	I _F = 8 A	-	2.3	3.0	V				
		I _F = 8 A, T _J = 150 °C	-	1.4	1.7					
Develope legicome eviment	I _R	$V_R = V_R$ rated	-	0.3	50					
Reverse leakage current		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	35	500	μA				
Junction capacitance	C _T	V _R = 600 V	-	17	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	=.	nΗ				



DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 A, dI_F/dt = 100$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		15	19			
Reverse recovery time		$I_F = 8 A, dI_F/dt = 100$	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		16	24			
heverse recovery time	t _{rr}	T _J = 25 °C		-	17	-	ns		
		T _J = 125 °C	I _F = 8 A dI _F /dt = 200 A/µs	-	40	-			
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.3	-	A nC		
reak recovery current		T _J = 125 °C	$V_{\rm R} = 390 \text{ V}$	-	4.5	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VH = 000 V	-	20	-			
heverse recovery charge		T _J = 125 °C		-	100	-			
Reverse recovery time	t _{rr}		I _F = 8 A	-	31	-	ns		
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 600 A/\mu s$	-	12	-	Α		
Reverse recovery charge	Q _{rr}		V _R = 390 V	=	195	=	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction-to-case	R _{thJC}		ı	1.4	2	°C/W			
Thermal resistance, junction-to-ambient per leg	R _{thJA}	Typical socket mount	-	-	70				
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-				
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style 2L TO-220AC		8ET	X06				

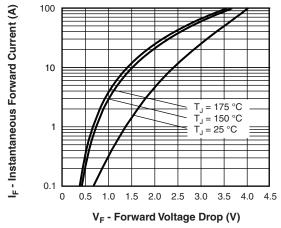


Fig. 1 - Typical Forward Voltage Drop Characteristics

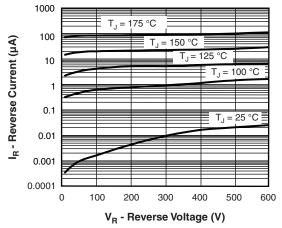


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

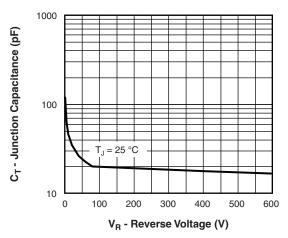


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

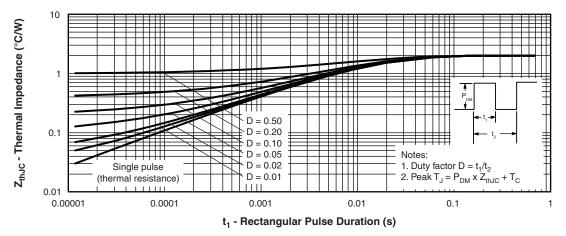


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

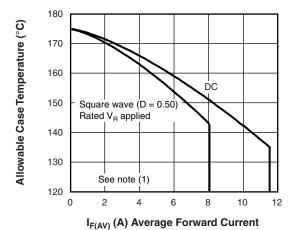


Fig. 5 - Maximum Allowable Case Temperature vs.

Average Forward Current

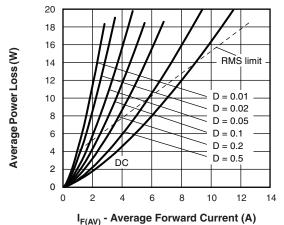
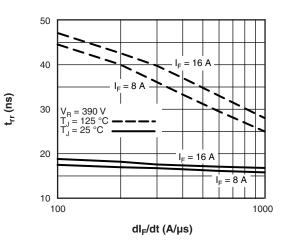


Fig. 6 - Forward Power Loss Characteristics

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (\text{Pd} + \text{Pd}_{\text{REV}}) \times R_{\text{thJC}}; \\ \text{Pd} = & \text{forward power loss} = I_{\text{F(AV)}} \times V_{\text{FM}} \text{ at } (I_{\text{F(AV)}}/D) \text{ (see fig. 5)}; \\ \text{Pd}_{\text{REV}} = & \text{inverse power loss} = V_{\text{R1}} \times I_{\text{R}} \text{ (1 - D)}; I_{\text{R}} \text{ at } V_{\text{R1}} = \text{rated } V_{\text{R}} \\ \end{array}$





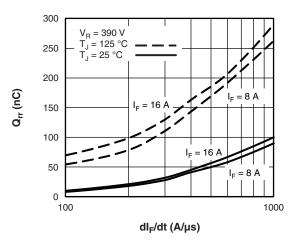
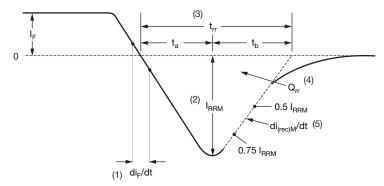


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_r$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

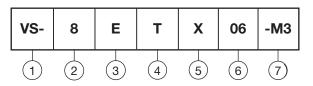
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - E = single

- T = TO-220, D²PAK (TO-263AB)

5 - X = hyperfast rectifier

6 - Voltage rating (06 = 600 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

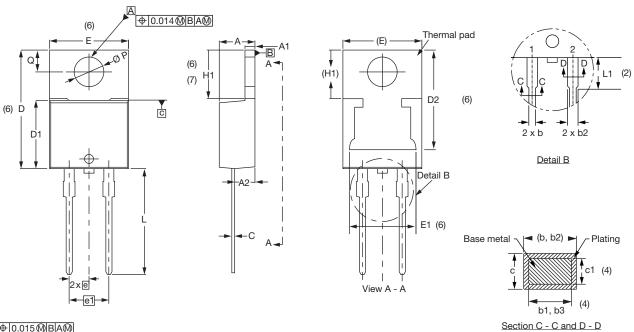
ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-8ETX06-M3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions <u>www.vishay.com/doc?96156</u>								
Part marking information	www.vishay.com/doc?95391							

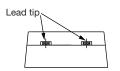


2L TO-220AC

DIMENSIONS in millimeters and inches



⊕ 0.015 **M** B A **M**



Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6	
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6	
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6	
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105		
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208		
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6, 7	
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552		
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2	
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154		
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118		
D1	8.38	9.02	0.330	0.355									

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2 (minimum)



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.